

TECHNICAL DATA
DATA SHEET 293, REV. A

HERMETIC POWER MOSFET N-CHANNEL

DESCRIPTION: A 100 VOLT, 0.07 OHM MOSFET IN A HERMETIC SHD-5B PACKAGE.**MAXIMUM RATINGS**ALL RATINGS ARE AT $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED.

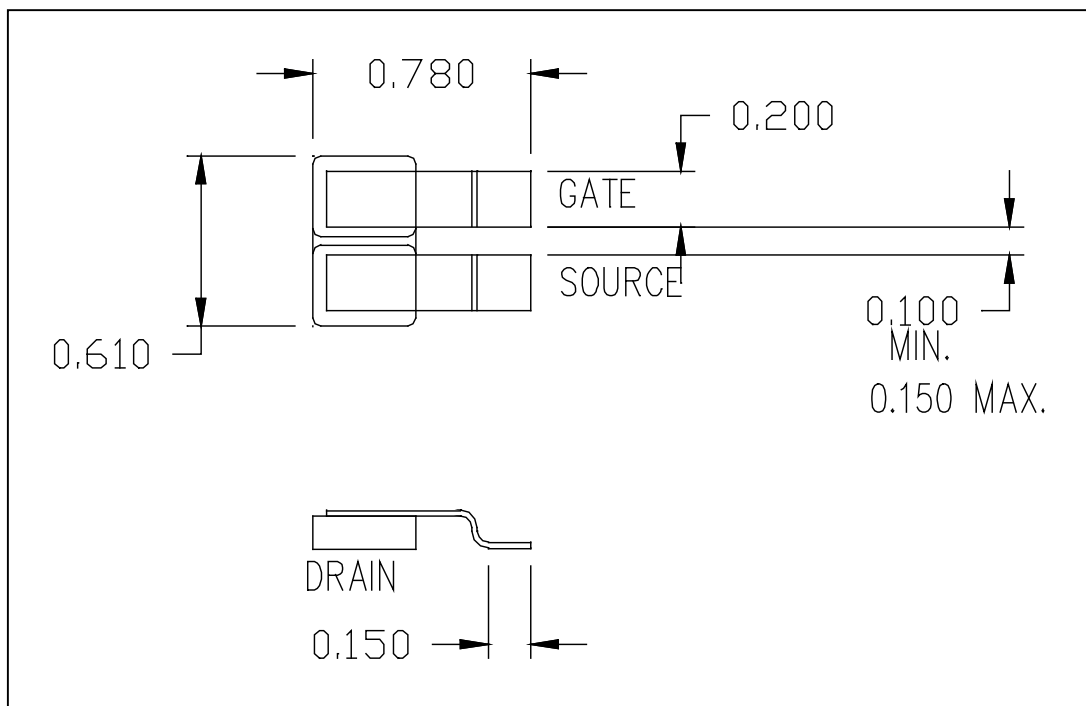
RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	± 20	Volts
CONTINUOUS DRAIN CURRENT @ $T_C = 25^\circ\text{C}$	I_D	-	-	34	Amps
PULSED DRAIN CURRENT @ $T_C = 100^\circ\text{C}$	I_{DM}	-	-	136	Amps(pk)
OPERATING AND STORAGE TEMPERATURE	T_{OP}/T_{STG}	-55	-	+150	$^\circ\text{C}$
TERMAL RESISTANCE JUNCTION TO CASE	$R_{\theta JC}$	-	-	0.39	$^\circ\text{C/W}$
TOTAL DEVICE DISSIPATION @ $T_C = 25^\circ\text{C}$	P_D	-	-	320	Watts

ELECTRICAL CHARACTERISTICS

DRAIN TO SOURCE BREAKDOWN VOLTAGE $V_{GS} = 0V, I_D = 1.0mA$	BV_{DSS}	100	-	-	Volts
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	2.0	-	4.0	
DRAIN TO SOURCE ON STATE RESISTANCE $V_{GS} = 10Vdc, I_D = 21A$ PULSE TEST, $t \leq 300 \mu s$, DUTY CYCLE $d \leq 2\%$	$R_{DS(ON)}$	-	-	0.07	Ω
ZERO GATE VOLTAGE DRAIN CURRENT $V_{DS} = 0.8 \times \text{Max. Rating}, V_{GS} = 0Vdc$ $V_{DS} = 0.8 \times \text{Max. Rating}$ $V_{GS} = 0Vdc, T_J = 125^\circ\text{C}$	I_{DSS}	-	-	25 250	μA
GATE TO BODY LEAKAGE CURRENT $V_{GS} = \pm 20Vdc$	I_{GSS}	-	-	± 100	nA
TOTAL GATE CHARGE $V_{GS} = 10Vdc$ GATE TO SOURCE CHARGE $V_{DS} = 0.5V \text{ Max. Rating},$ GATE TO DRAIN CHARGE $I_D = 27.4A$	Q_g Q_{gs} Q_{gd}	50 8.0 15	-	125 22 65	nC
TURN ON DELAY TIME $V_{DD} = 50V,$ RISE TIME $I_D = 34A,$ TURN OFF DELAY TIME $R_G = 2.35\Omega$ FALL TIME	$t_{d(ON)}$ t_r $t_{d(OFF)}$ t_f	-	-	35 190 170 130	nsec
FORWARD VOLTAGE $T_J = 25^\circ\text{C}, I_S = 34A, V_{GS} = 0V$ PULSE TEST, $t \leq 300 \mu s$, DUTY CYCLE $d \leq 2\%$	V_{SD}	-	-	1.8	Volts
REVERSE RECOVERY TIME $I_F = 34A$ REVERSE RECOVERY CHARGE $di/dt = 100A/\mu sec$ $V_{DD} \leq 50V$	t_{rr} Q_{rr}	- -	- -	500 2.9	nsec μC
INPUT CAPACITANCE $V_{DS} = 25Vdc,$ OUTPUT CAPACITANCE $V_{GS} = 0Vdc,$ REVERSE TRANSFER CAPACITANCE $f = 1 \text{ MHz}$	C_{iss} C_{oss} C_{rss}	-	3700 1100 200	-	pF

SENSITRON

DATA SHEET, 293 REV. A

MECHANICAL DIMENSIONS: in Inches**SHD-5B**

TECHNICAL DATA

DISCLAIMER:

- 1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the Sensitron Semiconductor sales department for the latest version of the datasheet(s).
- 2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.
- 3- In no event shall Sensitron Semiconductor be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). Sensitron Semiconductor assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.
- 4- In no event shall Sensitron Semiconductor be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.
- 5- No license is granted by the datasheet(s) under any patents or other rights of any third party or Sensitron Semiconductor.
- 6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of Sensitron Semiconductor.
- 7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.